

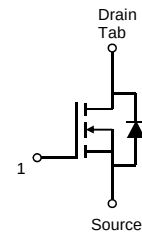
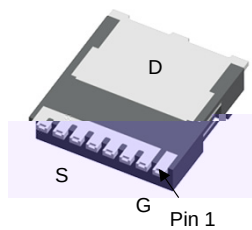
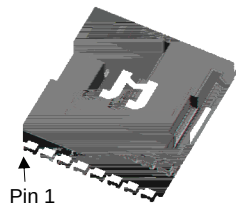


- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

	150	V
	3.2	V
	263	A
	3.3	mΩ

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics

PowerJE®10x12 Bottom

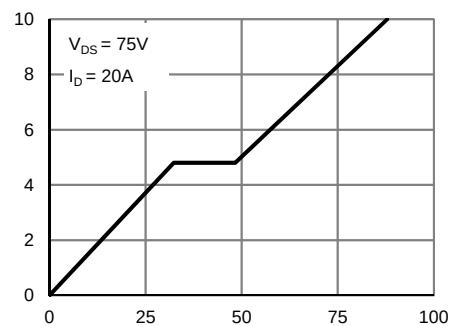
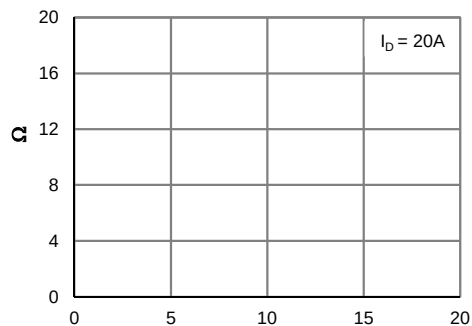


JMSH1504ATL-13	PowerJE®10x12 ⁽¹⁾	8	SH1504A	1	-55 to 175	13-inch Reel	2000
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Note 1: PowerJE® is a registered trademark of JieJie Micro., its package outline is compatible to that of TO-LeadLess (TOLL).

(@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

	V_{DS}		V
	V_{GS}		V
	I_{DM}		A
	I_{AS}		A
	E_{AS}		mJ
	T_J, T_{STG}		$^\circ\text{C}$

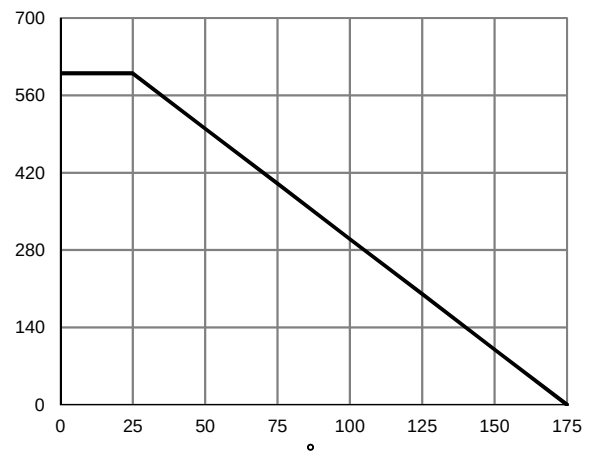
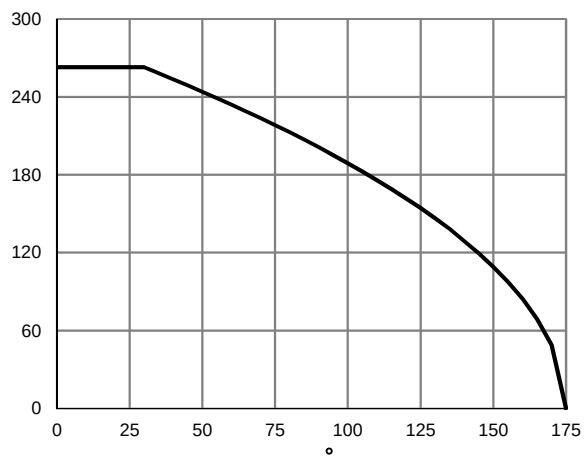
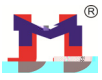


(@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$		1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$		± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.2	4.5 V
Static Drain-Source ON-Resistance	$R_{DS(on)}$			3.3	4.2 m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		65	S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$ Z		0.71	1.0 V
Diode Continuous Current	I_S			600	A
	C_{iss}			6540	pF
	C_{oss}			772	pF
	C_{rss}			6.7	pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.4	Ω
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g			88	nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$		57	nC
Gate Source Charge	Q_{gs}	$V_{DS} = 75\text{V}, I_D = 20\text{A}$		32	nC
Gate Drain Charge	Q_{gd}			16	nC
Turn-On Delay Time	$t_{D(on)}$			48	ns
Turn-On Rise Time	t_r	$V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$		90	ns
Turn-Off Delay Time	$t_{D(off)}$	$R_L = 3.75\Omega, R_{GEN} = 6\Omega$		94	ns
Turn-Off Fall Time	t_f			60	ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$		122	ns
Body Diode Reverse Recovery Charge	Q_{rr}			279	nC
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45		55	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	=		0.25	$^\circ\text{C/W}$

2. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.

[illegible]





DIM.	MIN.	MILLIMETER		MAX.
		NOM.		
A	2.20	2.30		2.40
b	0.70	0.80		0.90
b1	9.70	9.80		9.90
b2	0.42	0.46		0.50
c	0.40	0.50		0.60
D	10.28	10.38		10.58
D2		3.30		
E	9.70	9.90		10.10